

CMOS PARALLEL
SyncFIFOTM (CLOCKED FIFO)
512 x 18-BIT & 1024 x 18-BIT

IDT72215L IDT72225L

T-46-35

FEATURES

- 512 x 18-bit and 1024 x 18-bit memory array structures
- · 20ns read / write cycle time
- · Easily expandable in width
- · Read and write clocks can be independent or coincident
- · Dual-port zero fall-through time architecture
- · Programmable almost-empty and almost-full flags
- · Empty and Full flags signal FIFO status
- · Half-Full flag capability in a single device configuration
- Output enable puts output data bus in high impedance state
- Produced with advanced submicron CEMOS™ technology
- Available in a 68-lead flatpack (FP), pin grid array (PGA), and plastic leaded chip carrier (PLCC)
- Military product compliant to MIL-STD-883, Class B

DESCRIPTION

The IDT72215L and IDT72225L are very high speed, low-power first-in, first-out (FIFO) memories with read and write controls. The IDT72215L has a 512 x 18-bit memory array, while the IDT72225L has a 1024 x 18-bit memory array.

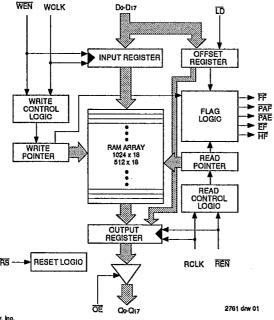
These FIFOs are applicable for a wide variety of data buffering needs, such as optical disk controllers, local area networks (LANs), and interprocessor communication.

Both FIFOs have 18-bit input and output ports. The input port is controlled by a free-running clock (WCLK) and a data input enable pin (\overline{WEN}). Data is written into the Synchronous FIFO on every clock when \overline{WEN} is asserted. The output port is controlled by another clock pin (RCLK) and another enable pin (\overline{REN}). The read clock can be tied to the write clock for single clock operation or the two clocks can run independent of one another for dual clock operation. An output enable pin (\overline{OE}) is provided on the read port for three-state control of the output.

The Synchronous FIFOs have two fixed flags, Empty (EF) and Full (FF), and two programmable flags, Almost-Empty (PAE) and Almost-Full (PAF). The loading of the programmable flag offsets can be controlled by a simple state machine and is initiated by asserting the load pin (LD). A Half-Full flag (HF) is also available.

The IDT72215L/72225L is fabricated using IDT's high speed submicron CEMOS™ technology. Military grade product is manufactured in compliance with the latest revision of MIL-STD-883, Class B.

FUNCTIONAL BLOCK DIAGRAM



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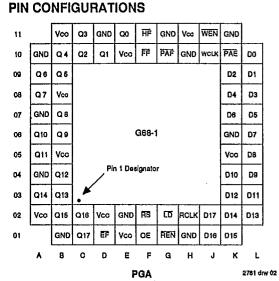
MILITARY AND COMMERCIAL TEMPERATURE RANGES

APRIL 1992

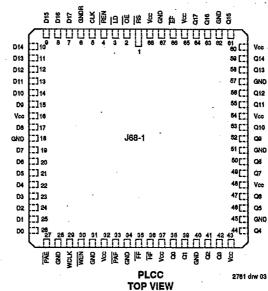
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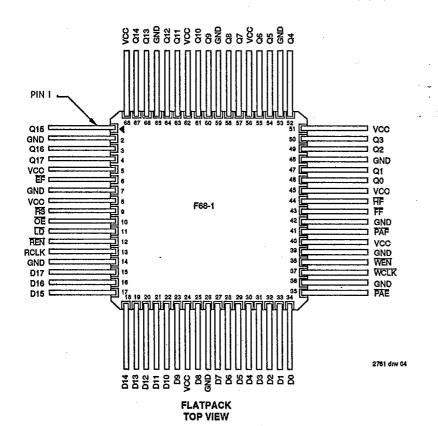
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TOP VIEW





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IDT72215L/72225L CMOS SYNCHRONOUS FIFO 512 x 18-BIT and 1024 x 18-BIT

MILITARY AND COMMERCIAL TEMPERATURE RANGES

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PIN DESCRIPTIONS

SYMBOL	NAME	VO	DESCRIPTION			
D0 - D17	inputs		Data inputs for 18-bit wide data,			
RS	Reset .	I	When RS is set low, internal read and write pointers are set to the first location of the RAM array FF and PAF go high, and PAE and EF go low. A reset is required before an initial WRITE after power-up.			
WCLK	Write Clock	-	When WEN is low, a write cycle is initiated on the low-to-high transition of the write clock WCLK, if the FIFO is not full.			
WEN	Write Enable	Ι	When WEN is low, data can be loaded into the FIFO on the low-to-high transition of every WCLk clock. When the FIFO is full (FF - low), the internal WRITE operation is blocked.			
RCLK	Read Clock	_	When REN is enabled (low), data can be read on the outputs on the low-to-high transition of the read clock RCLK, if the FIFO is not empty.			
REN	Read Enable		When REN is low, data can be read from the FIFO on the low-to-high transition of every RCLK clock. When REN is high, the output register holds the previous data. When the FIFO is empty (EF-low), the internal READ operation is blocked.			
ŌĒ	Output Enable	ì	When \overline{OE} is enabled (low), the parallel output buffers receive data from the output register. When \overline{OE} is disabled (high), the Q output bus is in a high impedance state.			
ĹĎ	Load	1	When LD is low, data on the inputs D0-D15 is written to the offset registers on the low-to-high transition of the WCLK.			
FF	Full Flag	0	When FF goes low, the device is full and further WRITE operations are inhibited. When FF is high, the device is not full. FF is synchronized with WCLK.			
ĒF	Empty Flag	0	When EF goes low, the device is empty and further READ operations are inhibited. When EF is high, the device is not empty. EF is synchronized with RCLK.			
PAF	Programmable Almost Full Flag	0	When PAF is low, the device is almost full based on the programmable full offset. If there is no offset specified, the default value is 63 for 72215, and 127 for 72225.			
PAE	Programmable Almost Empty Flag	0	When PAE is low, the device is almost empty based on the programmable empty offset. If there is no offset specified, the default value is 63 for 72215, and 127 for 72225.			
ĦĒ	Half-Full Flag	0	The device is more than half full when HF is low.			
Q0-Q17	Outputs	o	Data outputs for 18-bit wide data,			
Vcc	Power Supply		Nine +5 V power supply pins.			
GND	Ground		Eleven Ground pins.			

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IDT72215L/72225L CMOS SYNCHRONOUS FIFO 512 x 18-BIT and 1024 x 18-BIT

MILITARY AND COMMERCIAL TEMPERATURE RANGES

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ABSOLUTE MAXIMUM RATINGS⁽¹⁾

Symbol	Rating	Commercial	Military	Unit
VTERM	Terminal Voltage with Respect to GND	-0.5 to +7.0	-0.5 to +7.0	٧
TA	Operating Temperature	0 to +70	-55 to +125	°C
TBIAS	Temperature Under Bias	-55 to +125	-65 to +135	°C
Тѕта	Storage Temperature	-55 to +125	-65 to +135	°C
lout	DC Output Current	50	50	mA

2761 tbi 02 NOTE:

1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of the specification is not Implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vссм	Military Supply Voltage	4.5	5.0	5.5	٧
Vccc	Commercial Supply Voltage	4.5	5,0	5.5	٧
GND	Supply Voltage	0	0	0	٧
ViH	Input High Voltage Commercial	2.0	_	_	٧
VIH	Input High Voltage Military	2.2	-	_	٧
VIL(1)	Input Low Voltage Commercial & Military		-	0.8	٧

NOTE:

1. 1.5V undershoots are allowed for 10ns once per cycle.

2761 tol 03

DC ELECTRICAL CHARACTERISTICS

(Commercial: Vcc = 5V ± 10%, TA = 0°C to +70°C; Military: Vcc = 5V ± 10%, TA = -55°C to +125°C)

		IDT72215L/72225L Commercial tclk = 20, 25, 35, 50ns			IDT72215L/72225L Military tcLK = 25, 35, 50ns				
Symbol	Parameter	Min.	Тур.	Max.	Min.	Тур.	Max.	Unit	
[LI ⁽¹⁾	Input Leakage Current (Any Input)	-1		-1	-10	_	10	μА	
(LO ⁽²⁾	Output Leakage Current	-10	_	10	-10	_	10	μА	
Vон	Output Logic "1" Voltage, loн = -2 mA	2.4			2.4		_	٧	
Vol	Output Logic "0" Voltage, IoL = 8 mA		_	0.4		-	0.4	٧	
Icc1 ⁽³⁾	Active Power Supply Current		-	250	_	_	250	mA	
ICC2 ⁽³⁾	Average Standby Current (All Inputs = Vco - 0.2V, except RCLK and WCLK wchich are free running)	_	-	70	1	_	85	mA	

- 1. Measurements with 0.4 ≤ ViN ≤ Vcc.
- OE ≥ ViH, 0.4 ≤ VouT ≤ Vco.
 Tested at f = 20MHz with outputs open.

CAPACITANCE (TA = +25°C, f = 1.0MHz)

Symbol	Parameter ⁽¹⁾	Conditions	Max.	Unit
CIN ⁽¹⁾	Input Capacitance	VIN = 0V	10	pF
Cout ^(1,2)	Output Capacitance	Vout = 0V	10	ρF
NOTEO.				2761 tbl

NOTES:

Characterized values, not currently tested.
 With output deselected, (OE = high).



2761 tbl 04

IDT72215L/72225L CMOS SYNCHRONOUS FIFO 512 x 18-BIT and 1024 x 18-BIT

MILITARY AND COMMERCIAL TEMPERATURE RANGES

AC ELECTRICAL CHARACTERISTICS (1)

(Commercial: $Vcc = 5V \pm 10\%$, $TA = 0^{\circ}C$ to $+ 70^{\circ}C$; Military: $Vcc = 5V \pm 10\%$, $TA = -55^{\circ}C$ to $+125^{\circ}C$)

		Com'l. 72215L/25L20		Commercial & Military 72215L/25L25 72215L/25L35 72215L/25L50						
Symbol	Parameter	/2215L	Max.	Min.	Max.	/2215t Min,	Max.	Min.	Max.	Unit
ſs	Clock Cycle Frequency	_	50	_	40	_	28.6	_	20	MHz
tA	Data Access Time	-	13		15	_	20	_	25	ns
tolk	Clock Cycle Time	20		25	-	35	_	50	_	ns
tclkh	Clock High Time	8	_	10		14		20		ns
tclkl.	Clock Low Time	10		10		14		20	_	ns
tos	Data Set-up Time	7	-	8	+	10	_	10	_	ns
ton	Data Hold Time ⁽¹⁾	1		1_		2		2		ns
tens	Enable Set-up Time	7	_	9	_	11	_	12	_	ns
tenh	Enable Hold Time	1	_	1		2		2		ns
tas	Reset Pulse Width	20	_	25		35		50		ns
tass	Reset Set-up Time	12		15	_	20		30		ns
tasa	Reset Recovery Time	15	_	20		25	_	35		ns
trsf	Reset to Flag and Output Time		20		25		35		50	ns
tolz	Output Enable to Output in Low Z ⁽³⁾	0		0		0		0		ns
toe	Output Enable to Output Valid	_	9	_	12	-	- 17	_	20	ns
tonz	Output Enable to Output in High Z ⁽³⁾	1	9	1	12	1	17	1	20	ns
twff	Write Clock to Full Flag		14		16	-	20	_	30	ns
taer	Read Clock to Empty Flag	_	12		15		20	_	30	ns
TPAE	Clock to Programmable Almost-Empty Flag		20		22	_	30	-	35	ns
tpaf	Clock to Programmable Almost-Full Flag		20	-	22	-	30		35	ns
tHF	Clock to Half-Full Flag		20		22		30		35	ns
tskw1	Skew time between Read Clock & Write Clock for Full Flag	14.		16 -	_	18	_	20	_	ns
tskw1	Skew time between Read Clock & Write Clock for Empty Flag	14	_	16	_	18		20		ns

NOTES:

- 1. Allow an additional two (2) ns hold time when programming the offset registers.
 2. Pulse widths less than minimum values are not allowed.
 3. Values guaranteed by design, not 100% tested.

AC TEST CONDITIONS

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	See Figure 1

2761 tbl 07

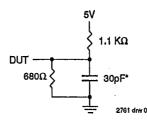


Figure 1. Output Load

* Includes jig and scope capacitances.

2761 tbl 06

SIGNAL DESCRIPTIONS:

Inputs

DATA IN (D0 - D17)

Data inputs for 18-bit wide data.

Controls:

RESET (RS)

Reset is accomplished whenever the Reset ($\overline{\mbox{RS}}$) input is taken to a low state. During reset, both internal read and write pointers are set to the first location. A reset is required after power up before a write operation can take place. The Full Flag ($\overline{\mbox{FF}}$), Half-Full Flag ($\overline{\mbox{HF}}$), and Programmable Almost Full Flag ($\overline{\mbox{PAF}}$) will be reset to high after tRSF. The Empty Flag ($\overline{\mbox{PAE}}$) and Programmable Almost Empty Flag ($\overline{\mbox{PAE}}$) will be reset to low after tRSF.

WRITE CLOCK (WCLK)

A write cycle is initiated on the low-to-high transition of the write clock (WCLK) if \overline{WEN} is low. Data set-up and hold times must be met in respect to the low-to-high transition of the write clock (WCLK).

WRITE ENABLE (WEN)

When Write Enable (WEN) is low, data can be loaded into the input register and RAM array on the low-to-high transition of every write clock (WCLK). Data is stored in the RAM array sequentially and independently of any on-going read operation.

When Write Enable (WEN) is high, the input register holds the previous data and no new data is allowed to be loaded into the register.

To prevent data overflow, the Full Flag (FF) will go low, inhibiting further write operations. Upon the completion of a valid read cycle, the Full Flag (FF) will go high after tWFF, allowing a write to begin. Write Enable (WEN) is ignored when the FIFO is full.

READ CLOCK (RCLK)

Data can be read on the outputs on the low-to-high transition of the read clock (RCLK) if REN is low.

READ ENABLE (REN)

When Read Enable (\overline{REN}) is low, data that has been stored in the output register on the previous read cycle can be read on the outputs on the low-to-high transition of every read clock (RCLK), if Output Enable (\overline{OE}) is enabled. At the same time, data is read from the RAM array to the output register on the low-to-high transition of the read clock (RCLK).

When Read Enable (REN) is high, the output register holds the previous data and no new data is allowed to be loaded into the register.

When all the data has been read from the FIFO, the Empty Flag (EF) will go low, inhibiting further read operations. Once a write is performed, the Empty Flag (EF) will go high after t_{REF} and a read can begin. Read Enable (REN) is ignored when the FIFO is empty.

OUTPUT ENABLE (OE)

When Output Enable (\overline{OE}) is enabled (low), the parallel output buffers receive data from the output register. When Output Enable (\overline{OE}) is disabled (high), the Q output data bus is in a high impedance state.

LOAD (LD)

The IDT72215L and IDT72225L devices contain two 16-bit offset registers and a 6-bit blank register which can be loaded with data from the data inputs, or read on the data outputs. When the Load ($\overline{\text{LD}}$) pin is set low and $\overline{\text{WEN}}$ is set low, data on the inputs D0 - D15 is written into the Empty offset register on the first low-to-high transition of the write clock (WCLK). When the Load ($\overline{\text{LD}}$) pin and Write Enable ($\overline{\text{WEN}}$) are held low then data is written into the Full offset register on the second low-to-high transition of the write clock (WCLK) and into the blank register on the third transition. The blank register must be written with all zeros. The fourth transition of the write clock (WCLK) again writes to the Empty offset register.

However, writing all offset registers does not have to occur at one time. One or two offset registers can be written and then by bringing the Load ($\overline{\text{LD}}$) pin high, the FIFO is returned to normal read/write operation. When the Load ($\overline{\text{LD}}$) pin is set low, and Write Enable ($\overline{\text{WEN}}$) is low, the next offset register in sequence is written.

The contents of the offset registers can be read on the output lines when the Load ($\overline{\text{LD}}$) pin is set low and $\overline{\text{REN}}$ is set low. Data can be read on the low-to-high transition of the read clock (RCLK), when $\overline{\text{REN}}$ is enabled (low).

A read and a write should not be performed simultaneously to the offset registers.

Outputs:

FULL FLAG (FF)

The Full Flag (FF) will go low, inhibiting further write operation, indicating that the device is full. If no reads are performed after Reset (RS), the Full Flag (FF) will go low after 512 writes for the IDT72215L and 1024 writes for the IDT72225L.

The Full Flag (FF) is updated on the low-to-high transition of the write clock (WCLK).

EMPTY FLAG (EF)

The Empty Flag (EF) will go low, inhibiting further read operations, indicating the device is empty.

The Empty Flag (EF) is updated on the low-to-high transition of the read clock (RCLK).



SYNCHRONOUS FIFO 512 x 18-BIT and 1024 x 18-BIT PROGRAMMABLE ALMOST FULL FLAG (PAF)

The Programmable Almost Full Flag (PAF) will go low when the FIFO reaches the Almost Full condition. If no reads are performed after Reset (RS), the Programmable Almost Full Flag (PAF) will go low after (512 - m) writes for the IDT72215L and (1024 - m) writes for the IDT72225L. The offset 'm' is defined in the FULL offset register.

If there is no Full offset specified, the Programmable Almost Full Flag (PAF) default value is 63 for 72215L, and 127 for 72225L.

The Programmable Almost Full Flag (PAF) going low is updated on the low-to-high transition of the write clock (WCLK). PAF is reset to high on the low-to-high transition of the read clock (RCLK).

PROGRAMMABLE ALMOST EMPTY FLAG (PAE)

The Programmable Almost Empty Flag (PAE) will go low when the read pointer is 'n' locations less than the write pointer. The offset 'n' is defined in the EMPTY offset register. If no reads are performed after Reset (RS), the Programmable Almost Empty Flag (PAE) will go high after n writes for both the IDT72215L and the IDT72225L. The Programmable Almost

Empty Flag (PAE) will be low when the FIFO is empty up to n writes, if the read pointer is not moved.

If there is no Empty offset specified, the Programmable Almost Empty Flag (PAE) default value is 63 for 72215L, and 127 for 72225L.

The Programmable Almost Empty Flag (PAE) going low is updated on the low-to-high transition of the read clock (RCLK). PAE is reset to high on the low-to-high transition of the wirte clock (WCLK).

HALF-FULL FLAG (HF)

After half of the memory is filled, and at the low-to-high transition of the next write cycle, the Half-Full Flag (HF) goes low and will remain set until the difference between the write pointer and read pointer is less than or equal to one half of the total memory of the device. The Half-Full Flag (HF) is then reset to high by the low-to-high transition of the read clock (RCLK).

DATA OUTPUTS (Q0 - Q17)

Qo - Q17 are data outputs for 18-bit wide data.

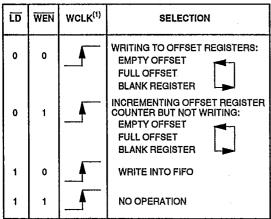


Figure 2. Write Offset Register

2761 tbl 08

NOTE:

1. The same selection sequence applies to reading from the register. REN is enabled and read is performed on the low-to-high transition of RCLK.

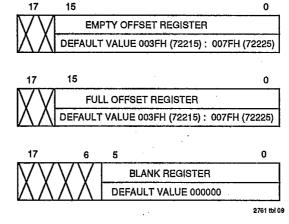


Figure 3. Offset Register Location and Default Values

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t_{RSR}

~ 0E=0

Figure 5. Reset Timing⁽²⁾

2761 drw 06

NOTES:

NOTES: 1. After reset, the outputs will be low if $\overline{OE} = 0$ and tri-state if $\overline{OE} = 1$. 2. The clocks (RCLK, WCLK) can be free-running during reset.

t_{RSF}



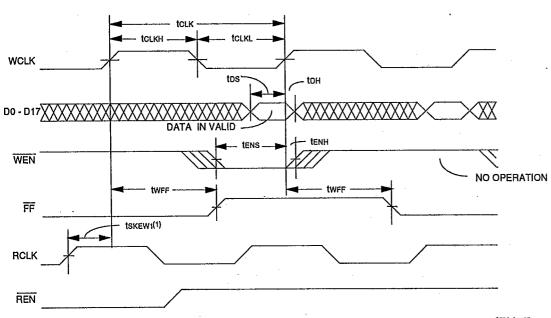


Figure 6. Write Cycle Timing

2761 dry 07

NOTE:

1. tskewi is the minimum time between a rising RCLK edge and a rising WCLK edge to guarantee FF will go high during the current clock cycle. If the time between therising edge of RCLK and the rising edge of WCLK is less than tskewi, then FF may not change state until the next WCLK edge.

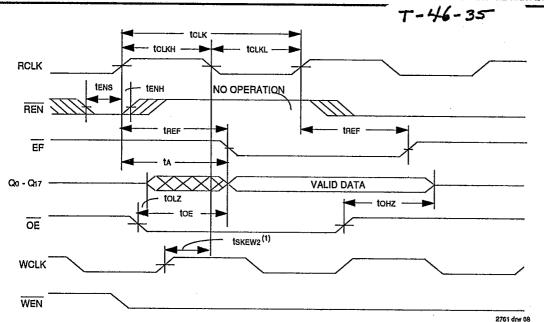


Figure 7. Read Cycle Timing

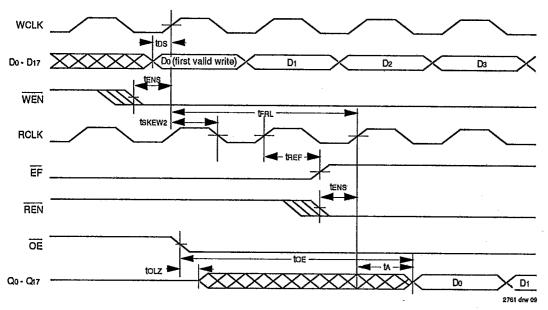


Figure 8. First Data Word Latency after Reset with Simultaneous Read and Write

NOTE:

1. When tskew₂ ≥ minimum specification, tral (maximum) = 1.5 * tclk + tskew₂. When tskew₂ < minimum specification, tral (maximum) = either 2.5 * tclk + tskew₂ or 1.5 * tClK + tskew₂. The Latency Timing applies only at the Empty Boundary (EF = LOW).

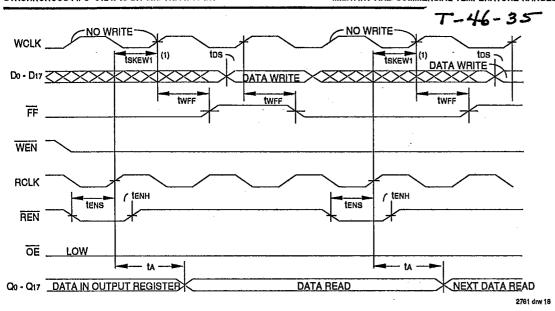


Figure 9. Full Flag Timing

NOTE:

1. tskew is the minimum time between a rising RCLK edge and a rising WCLK edge to guarantee FF will go high during the current clock cycle. If the time between therising edge of RCLK and the rising edge of WCLK is less than tskew, then FF may not change state until the next WCLK edge.



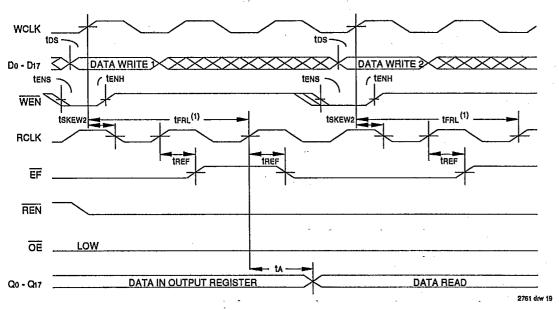


Figure 10. Empty Flag Timing

NOTE:

1. When tskew₂ ≥ minimum specification, trat (maximum) = 1.5 * totk + tskew₂. When tskew₂ < minimum specification, trat (maximum) = either 2.5 * totk + tskew₂ or 1.5 * totk + tskew₂. The Latency Timing applies only at the Empty Boundary (EF = LOW).

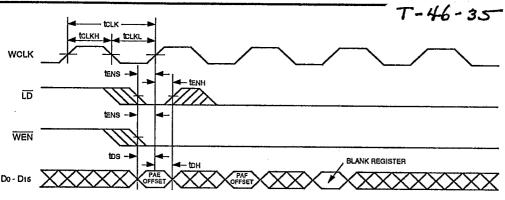


Figure 11. Write Programmable Registers

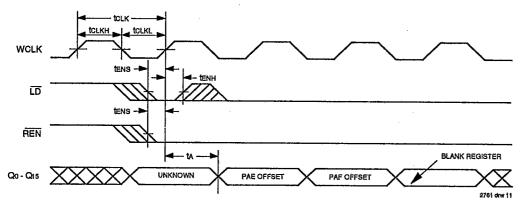
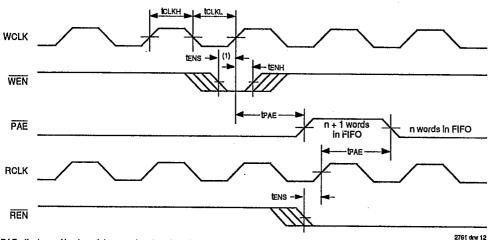


Figure 12. Read Programmable Registers



NOTE 1: PAE offset = n. Number of data words written into FIFO already = n.

Figure 13. Programmable Almost Empty Flag Timing

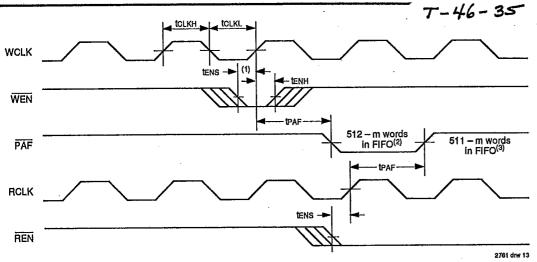


Figure 14. Programmable Almost Full Flag Timing

NOTES:

- PAF offset = m. Number of data words written into FiFO already = 511 m for the IDT72215L and 1023 m for the IDT72225L. 512 m words in FiFO for IDT72215L. 1024 m words in FIFO for IDT72225L. 511 m words in FIFO for IDT72215L. 1023 m words in FIFO for IDT72225L.
- 1. 2. 3.

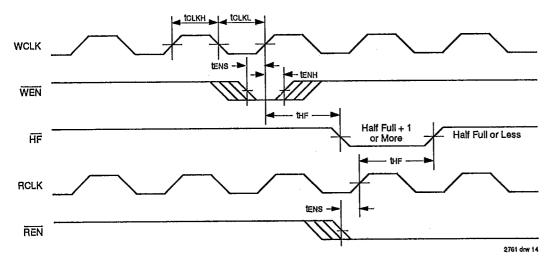


Figure 15. Half-Full Flag Timing



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IDT72215L/72225L CMOS SYNCHRONOUS FIFO 512 x 18-BIT and 1024 x 18-BIT

MILITARY AND COMMERCIAL TEMPERATURE RANGES

OPERATING CONFIGURATIONS:

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SINGLE DEVICE CONFIGURATION

A single IDT72215/72225 may be used when the application requirements are for 512/1024 words or less.

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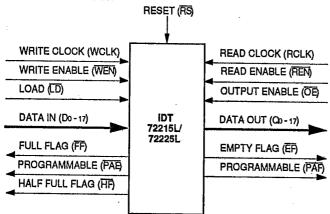


Figure 16. Block Diagram of Single 512 x 18/ 1024 x 18 Synchronous FIFO

IDT72215L/72225L CMOS

SYNCHRONOUS FIFO 512 x 18-BIT and 1024 x 18-BIT WIDTH EXPANSION CONFIGURATION

Word width may be increased simply by connecting the corresponding input control signals of multiple devices. Asynchronous status flags (PAE, HF, and PAF) can be detected from any one device. Synchronous status flags (EF and FF) should be gated through an AND gate because the

flag deassertions may vary among different FIFOs by one cycle. Figure 17 demonstrates a 36-word width by using two IDT72215L/72225Ls. Any word width can be attained by adding additional IDT72215L/72225Ls. Please see the Application Note AN-83 "Width Expansion of SyncFIFOs (Clocked FIFOs).

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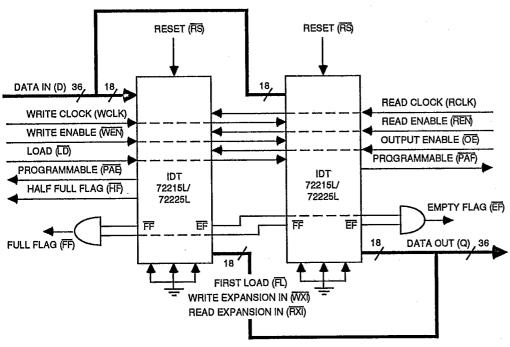




Figure 17. Block Diagram of 512 x 36/ 1024 x 36 Synchronous FIFO Memory Used in a Width Expansion Configuration

1. Flag detection is accomplished by monitoring the flag signals on either (any) device used in width expansion configuration. Do not connect any output control signals together.

DEPTH EXPANSION

The IDT72215L/72225L can be adapted to applications when the requirements are for greater than 512/1024 words. Depth expansion is possible by using expansion logic to direct the flow of data. A typical application would have the expansion logic alternate data accesses from one device to the next

in a sequential manner. Please contact IDT Applications Engineering for details.

The 72215LB/72225LB Depth Expandable versions of this part incorporate an on-chip depth expansion technique. Please see the 72215LB/72225LB data sheet for details. The 72215LB/72225LB version will supersede this part.

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